

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE

# 2SK1530

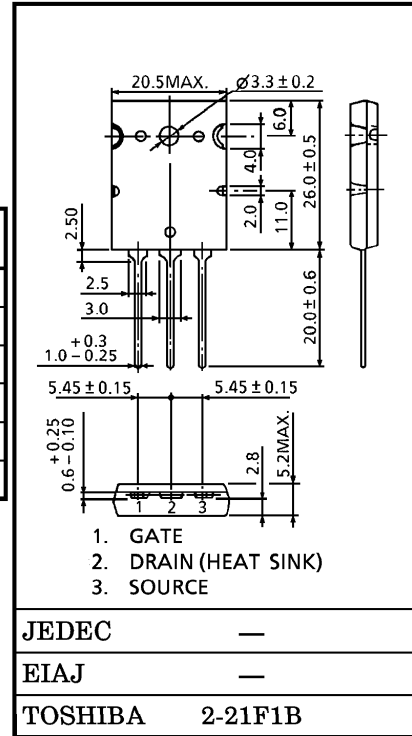
HIGH POWER AMPLIFIER APPLICATION

Unit in mm

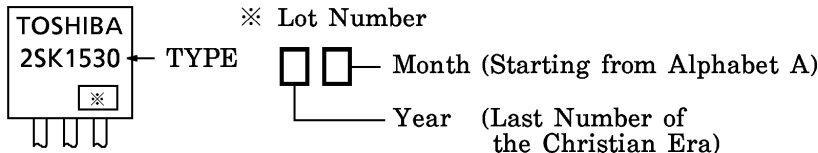
- High Breakdown Voltage :  $V_{DSS}=200V$
- High Forward Transfer Admittance :  $|Y_{fs}|=5.0S$  (Typ.)
- Complementary to 2SJ201

MAXIMUM RATINGS ( $T_a = 25^\circ C$ )

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	$V_{DSS}$	200	V
Gate-Source Voltage	$V_{GSS}$	$\pm 20$	V
Drain Current	$I_D$	12	A
Drain Power Dissipation ( $T_c = 25^\circ C$ )	$P_D$	150	W
Channel Temperature	$T_c$	150	$^\circ C$
Storage Temperature Range	$T_{stg}$	$-55 \sim 150$	$^\circ C$



MARKING



JEDEC	—
EIAJ	—
TOSHIBA	2-21F1B

ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ C$ )

Weight : 9.75g

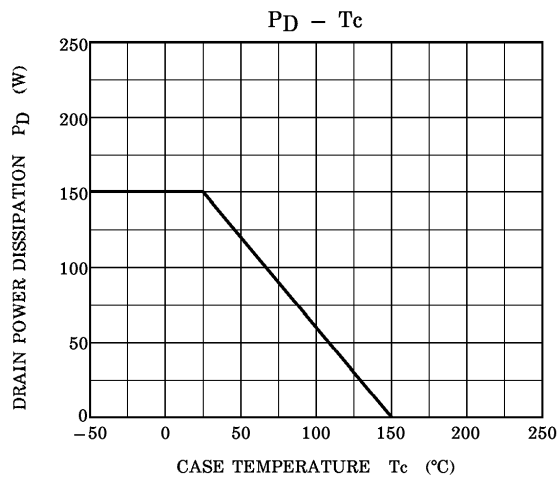
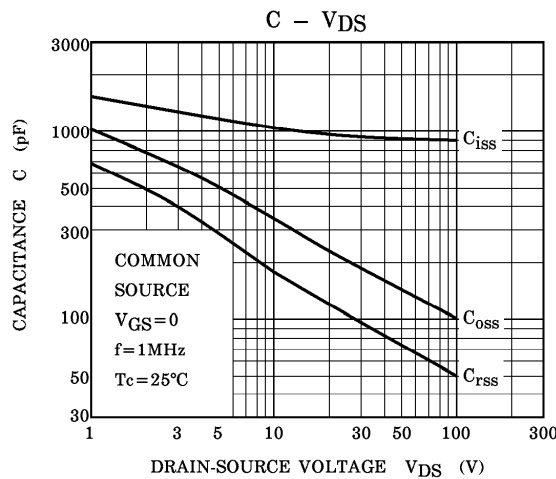
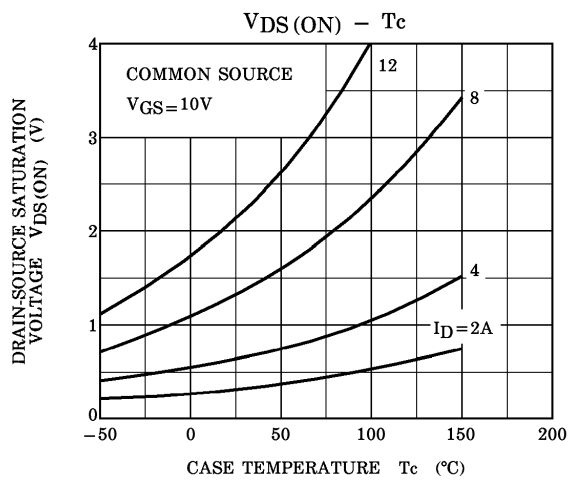
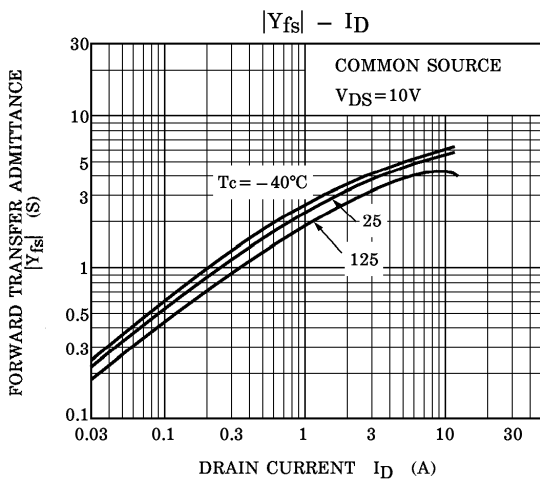
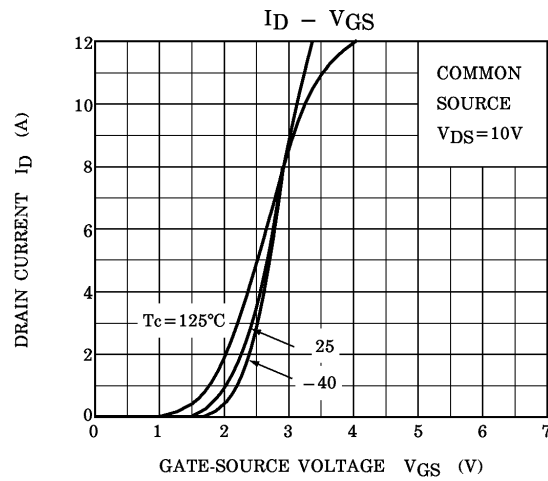
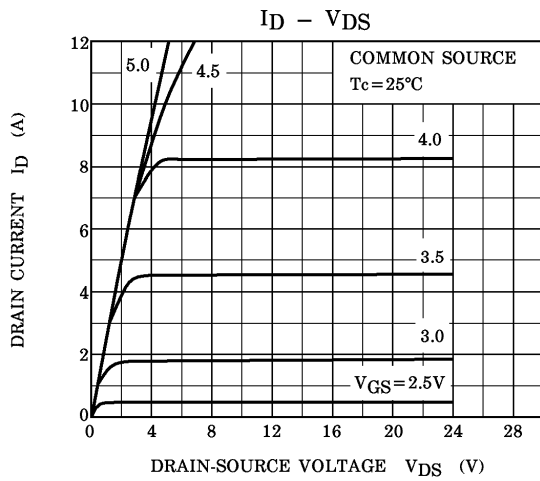
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Drain Cut-off Current	$I_{DSS}$	$V_{DS}=200V, V_{GS}=0$	—	—	1.0	mA
Gate Leakage Current	$I_{GSS}$	$V_{DS}=0V, V_{GS}=\pm 20V$	—	—	$\pm 0.5$	$\mu A$
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=10mA, V_{GS}=0$	200	—	—	V
Drain-Source Satruation Voltage	$V_{DS(ON)}$	$I_D=8A, V_{GS}=10V$	—	2.5	5.0	V
Gate-Source Cut-off Voltage (Note)	$V_{GS(OFF)}$	$V_{DS}=10V, I_D=0.1A$	0.8	—	2.8	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS}=10V, I_D=5A$	—	5.0	—	S
Input Capacitance	$C_{iss}$	$V_{DS}=30V, V_{GS}=0, f=1MHz$	—	900	—	pF
Output Capacitance	$C_{oss}$	$V_{DS}=30V, V_{GS}=0, f=1MHz$	—	180	—	pF
Reverse Transfer Capacitance	$C_{rss}$	$V_{DS}=30V, V_{GS}=0, f=1MHz$	—	100	—	pF

(Note)  $V_{GS(OFF)}$  Classification 0 : 0.8~1.6 Y : 1.4~2.8

**This transistor is an electrostatic sensitive devide.  
Please handle with caution.**

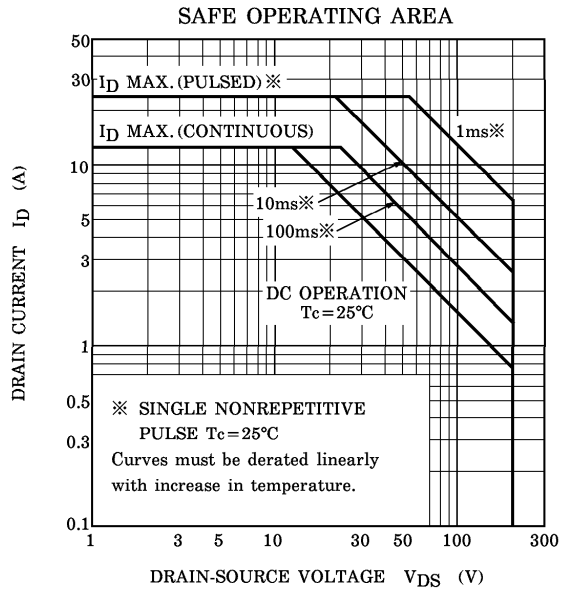
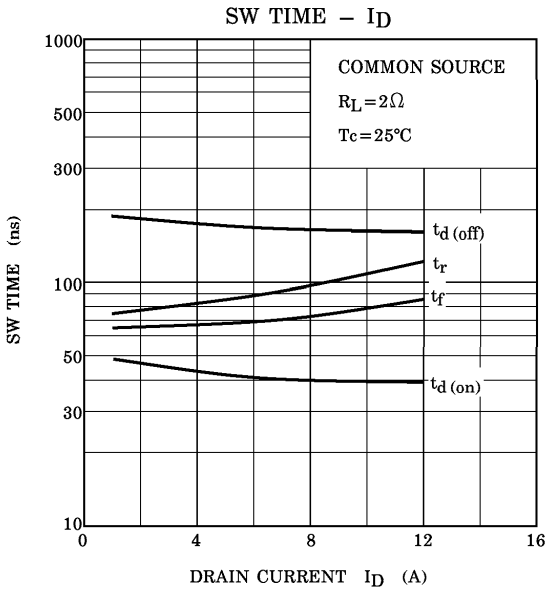
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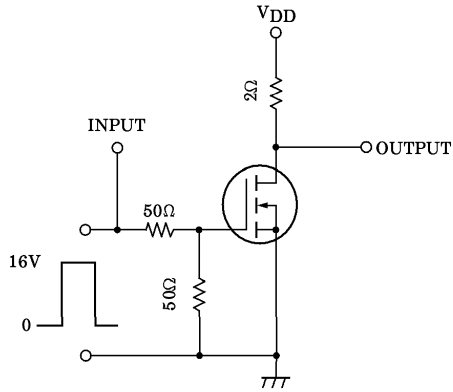


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SWITCHING TIME TEST CIRCUIT



WAVEFORMS

